



6N120

Power MOSFET

6.0A, 1200V N-CHANNEL POWER MOSFET

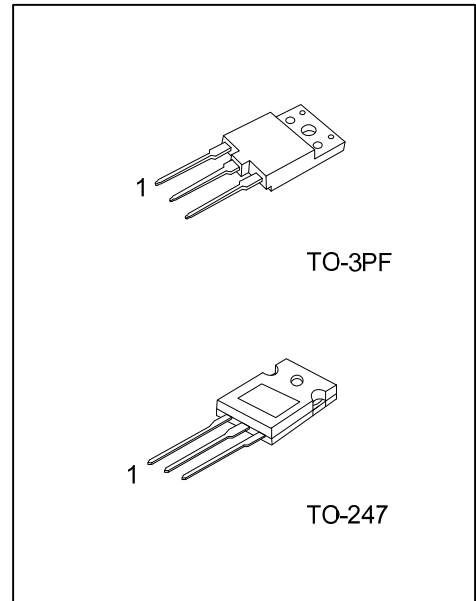
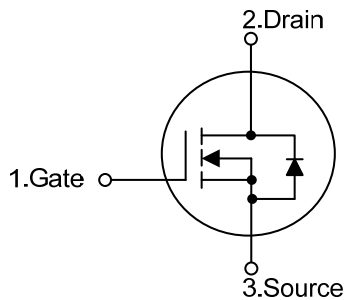
DESCRIPTION

The UTC **6N120** provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

FEATURES

- * $R_{DS(ON)} \leq 2.5 \Omega$ @ $V_{GS}=10V$, $I_D=3.0A$
- * Low Reverse Transfer Capacitance
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

SYMBOL



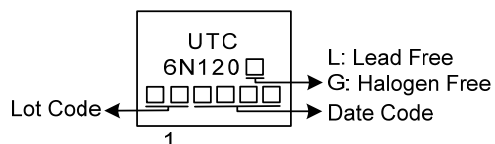
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
6N120L-T3F-T	6N120G-T3F-T	TO-3PF	G	D	S	Tube
6N120L-T47-T	6N120G-T47-T	TO-247	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

6N120G-T3F-T (1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube (2) T3F: TO-3PF, T47: TO-247 (3) G: Halogen Free and Lead Free, L: Lead Free
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MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DS}	1200	V
Gate-Source Voltage		V_{GS}	± 30	V
Drain Current	Continuous	I_D	6	A
	Pulsed (Note 2)	I_{DM}	12	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	360	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	1.5	V/ns
Power Dissipation	TO-3PF	P_D	65	W
	TO-247		160	W
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 30\text{mH}$, $I_{AS} = 4.9\text{A}$, $V_{DD} = 120\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$

4. $I_{SD} \leq 6.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^{\circ}\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-3PF	θ_{JA}	50	$^{\circ}\text{C}/\text{W}$
	TO-247		50	$^{\circ}\text{C}/\text{W}$
Junction to Case	TO-3PF	θ_{JC}	1.92	$^{\circ}\text{C}/\text{W}$
	TO-247		0.78	$^{\circ}\text{C}/\text{W}$

■ **ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	1200			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =1200V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	3.0		6.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =3.0A			2.5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1MHz		2040		pF
Output Capacitance	C _{OSS}			586		pF
Reverse Transfer Capacitance	C _{RSS}			356.8		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q _G	V _{DS} =100V, V _{GS} =10V, I _D =6.0A, I _G =1mA (Note 1, 2)		101		nC
Gate-Source Charge	Q _{GS}			21		nC
Gate-Drain Charge	Q _{GD}			57		nC
Turn-On Delay Time (Note 1)	t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =6.0A, R _G =25Ω (Note 1, 2)		34		ns
Turn-On Rise Time	t _R			80		ns
Turn-Off Delay Time	t _{D(OFF)}			270		ns
Turn-Off Fall Time	t _F			70		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I _S				6	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				12	A
Drain-Source Diode Forward Voltage (Note 1)	V _{SD}	I _S =6.0A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t _{rr}	I _S =6.0A, V _{GS} =0V,		0.84		μS
Body Diode Reverse Recovery Charge	Q _{rr}	dl _F /dt=100A/μs		15		μC

Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

D.U.T.

V_{DS}

I_{SD}

L

V_{DD}

R_G

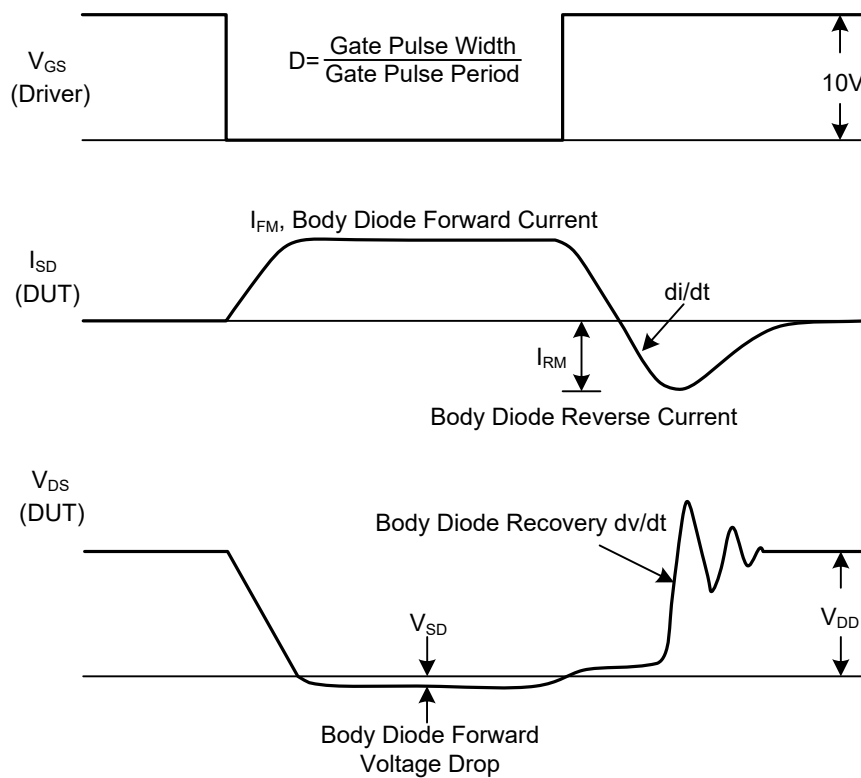
Driver

V_{GS}

Same Type as D.U.T.

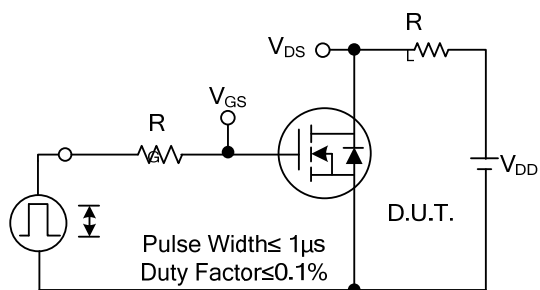
- * dv/dt controlled by R_G
- * I_{SD} controlled by pulse period
- * D.U.T.-Device Under Test

Peak Diode Recovery dv/dt Test Circuit

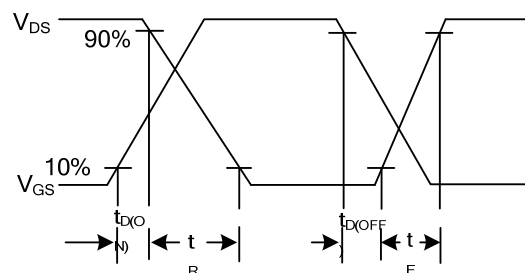


Peak Diode Recovery dv/dt Waveforms

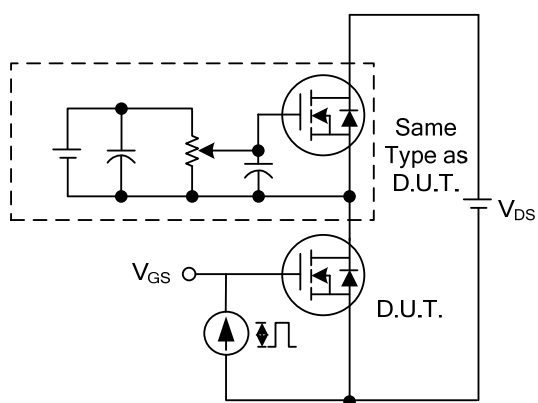
■ TEST CIRCUITS AND WAVEFORMS



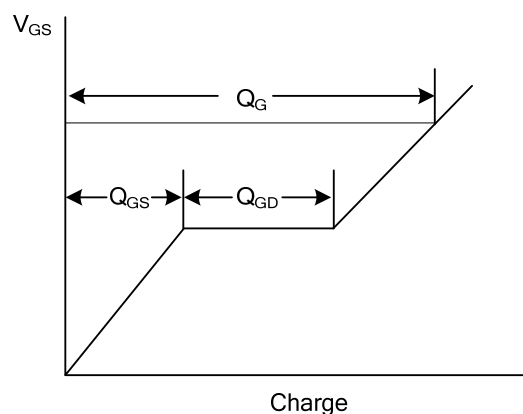
Switching Test Circuit



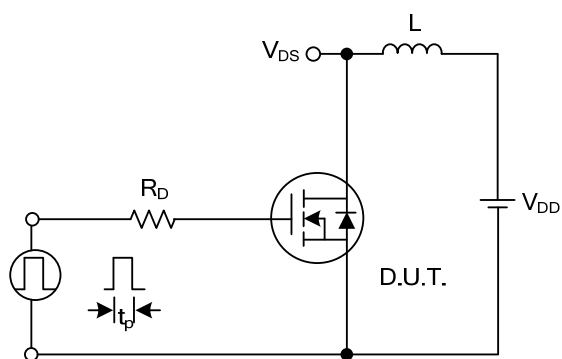
Switching Waveforms



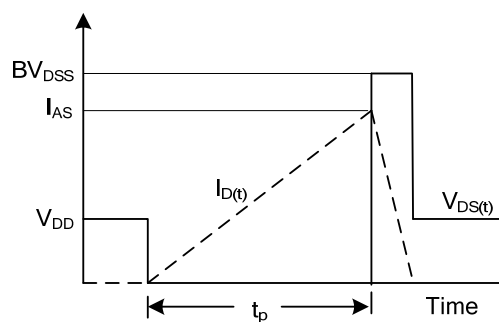
Gate Charge Test Circuit



Gate Charge Waveform

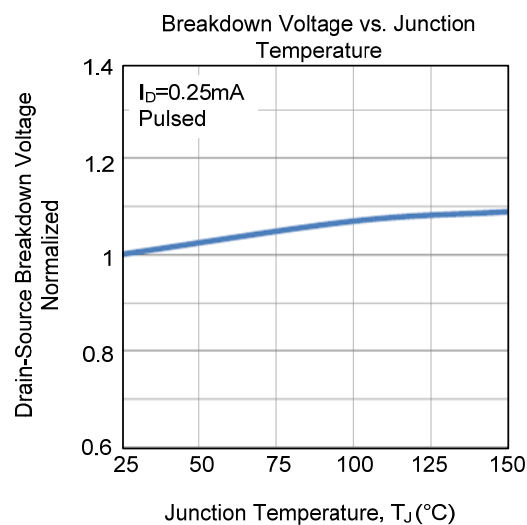
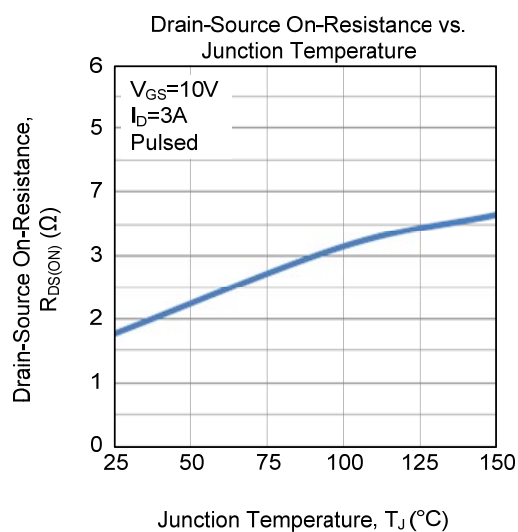
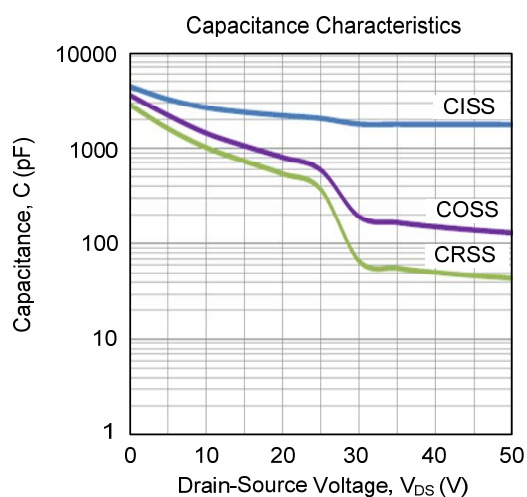
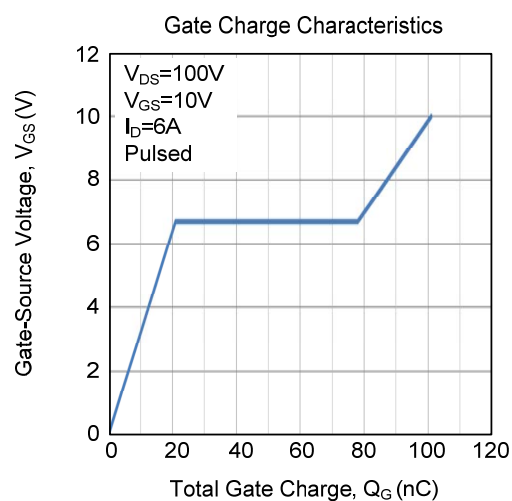
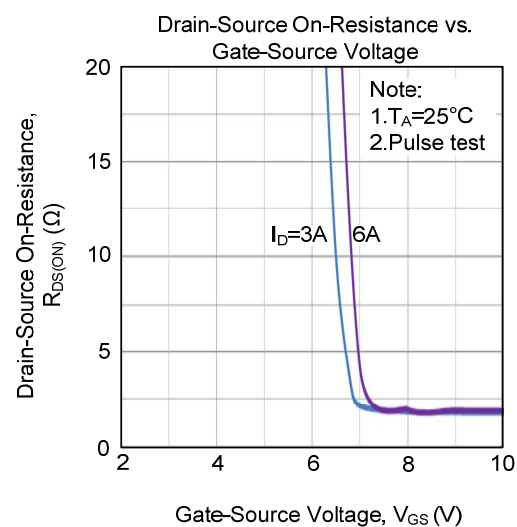
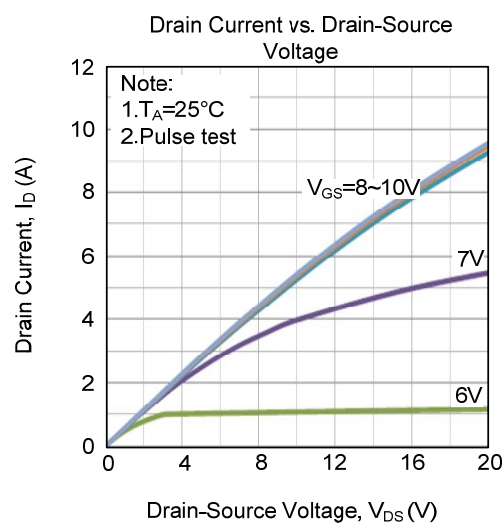


Unclamped Inductive Switching Test Circuit

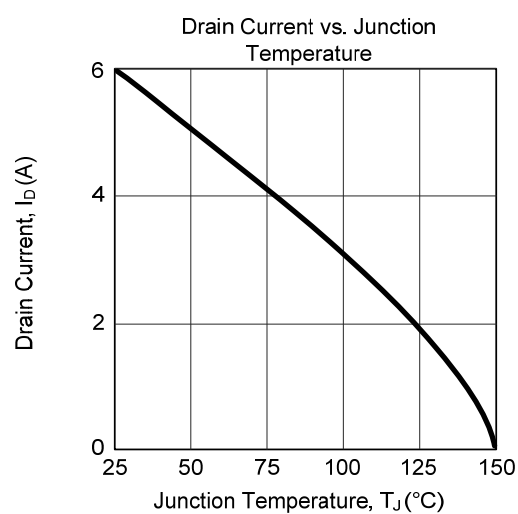
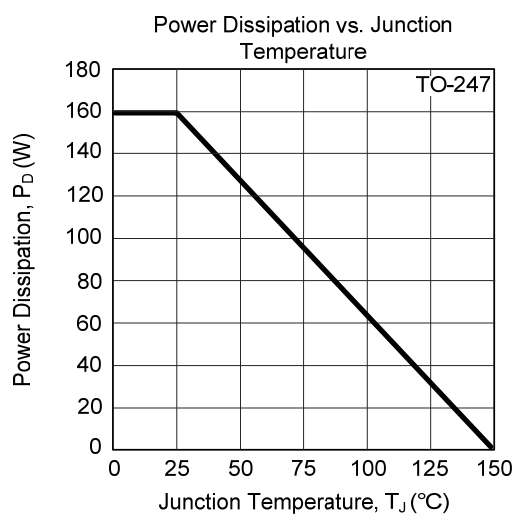
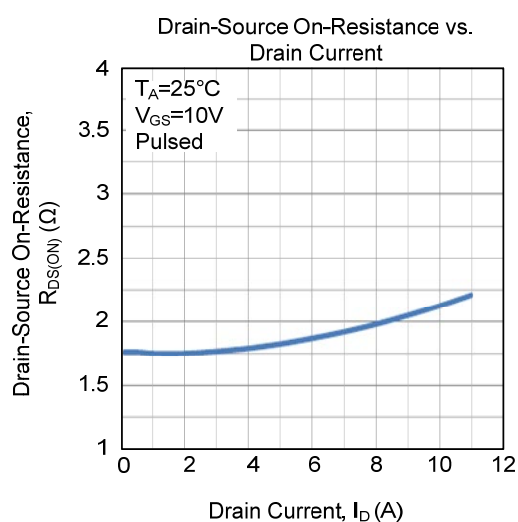
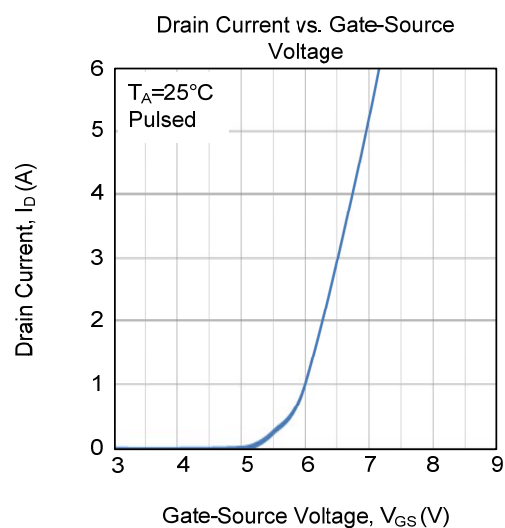
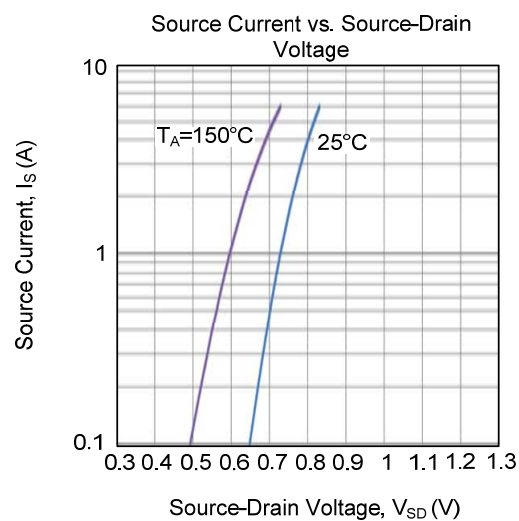
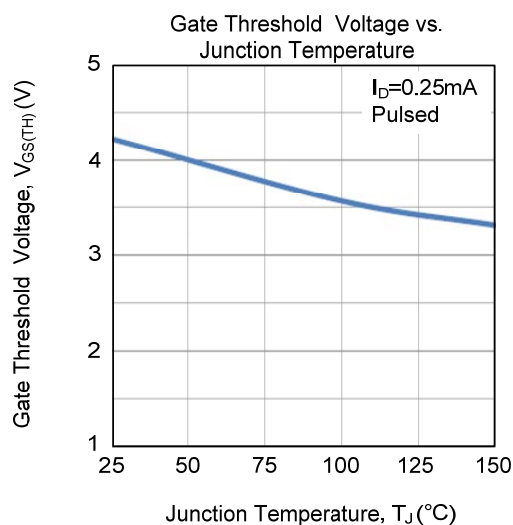


Unclamped Inductive Switching Waveforms

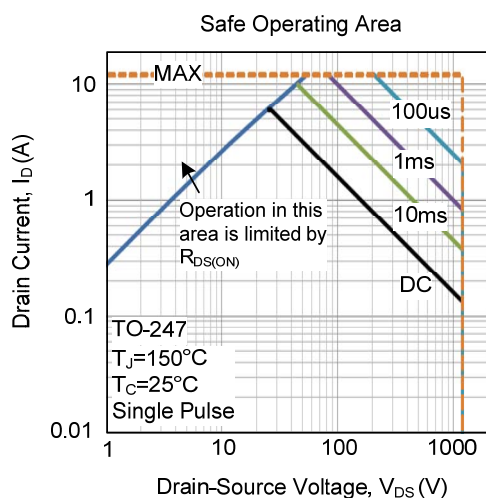
■ TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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